

Description

The HXY80N03D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

D G S

TO252-2L

General Features

 $V_{DS} = 30V I_{D} = 80 A$

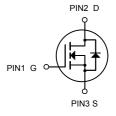
 $R_{DS(ON)} < 6.8 m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY80N03D	TO252-2L	80N03D XXX YYYY	2500

Absolute Maximum Ratings (T_C=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units		
VDS	Drain-Source Voltage	30	V		
Vgs	Gate-Source Voltage	±20	V		
	Drain Current – Continuous (T _C =25°C)	80	А		
ID	Ib Drain Current – Continuous (T _C =100°C)	51	А		
Ідм	Drain Current – Pulsed¹	Drain Current – Pulsed ¹ 320			
EAS	Single Pulse Avalanche Energy ²	88	mJ		
IAS	Single Pulse Avalanche Current ²	42	А		
_	Power Dissipation (T _C =25°C)	54	W		
PD	Power Dissipation – Derate above 25°C	0.43	W/°C		
Тѕтс	Storage Temperature Range	-55 to 150	°C		
TJ	Operating Junction Temperature Range	-55 to 150	°C		
R _θ JA	Thermal Resistance Junction to ambient	62	°C/W		
Rejc	Thermal Resistance Junction to Case	2.3	°C/W		

N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
△BVDSS/△TJ	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =1mA		0.04		V/°C
IDOO		V _{DS} =30V , V _{GS} =0V , T _J =25°C			1	uA
IDSS	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =125°C			10	uA
IGSS	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	-		±100	nA
DDC(ON)	Static Drain-Source On-Resistance ³	V _{GS} =10V , I _D =20A		5	6.8	mΩ
RDS(ON)		V_{GS} =4.5V , I_D =10A	-	6.5	9	mΩ
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA		1.6	2.5	>
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient			-4		mV/°C
gfs	Forward Transconductance	V _{DS} =10V , I _D =10A		18		S
Q_g	Total Gate Charge ^{3, 4}		-	11.1	-	
Qgs	Gate-Source Charge ^{3, 4}	V _{DS} =15V , V _{GS} =4.5V , I _D =20A	-	1.85	-	nC
Qgd	Gate-Drain Charge ^{3,4}]		6.8	1	
Td(on)	Turn-On Delay Time ^{3,4}		-	7.5	-	
Tr	Rise Time ^{3, 4}	V_{DD} =15V , V_{GS} =10V , R_G =3.3 Ω	-	14.5	1	ns
Td(off)	Turn-Off Delay Time ^{3,4}	I _D =15A	-	35.2	1	
T _f	Fall Time ^{3,4}			9.6		
Ciss	Input Capacitance	V _{DS} =25V , V _{GS} =0V , F=1MHz	-	1160	1	pF
Coss	Output Capacitance		-	200	-	
Crss	Reverse Transfer Capacitance			180		
R_g	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	2.5	1	Ω
EAS	Single Pulse Avalanche Energy	V _{DD} =25V, L=0.1mH, IAS=20A	20			mJ
IS	Continuous Source Current	V _G =V _D =0V , Force Current			80	Α
ISM	Pulsed Source Current ³				320	Α
VSD	Diode Forward Voltage ³	V _{GS} =0V , I _S =1A , T _J =25°C			1	٧
trr	Reverse Recovery Time	VGS=0V,IS=1A , di/dt=100A/μs T _J =25°C				ns
Q _{rr}	Reverse Recovery Charge					nC

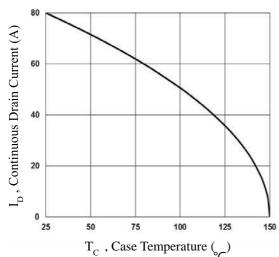


Fig.1 Continuous Drain Current vs. Tc

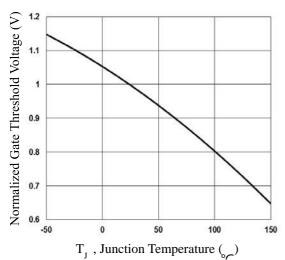


Fig. 3 Normalized Vth vs. Tj

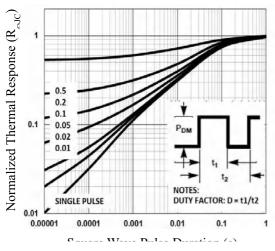


Fig.5 Normalized Transient Impedance

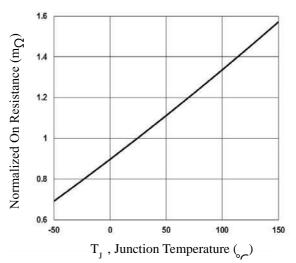


Fig.2 Normalized RDSON vs. Tj

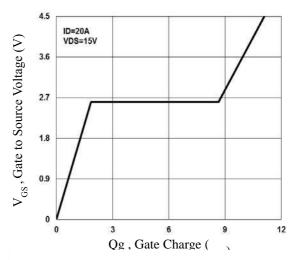


Fig. 4 Gate Charge Waveform

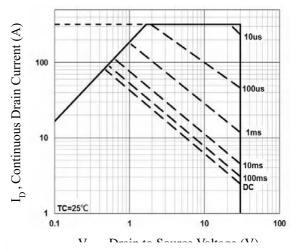
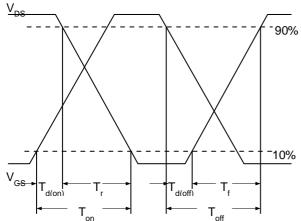


Fig.6 Maximum Safe Operation Area



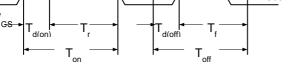


Fig. 7 Switching Time Waveform

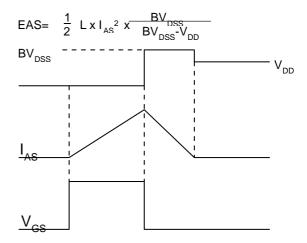
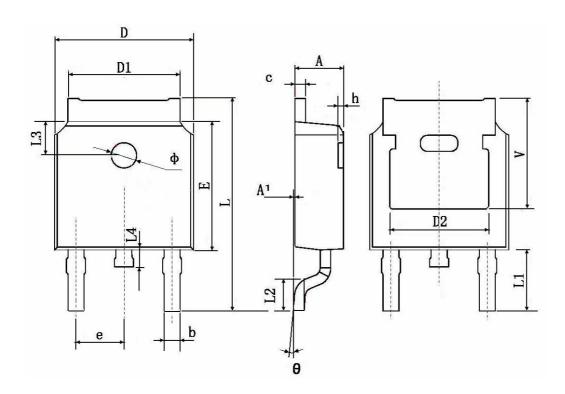


Fig. 8 EAS Waveform



TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211	TYP.	



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